Inventor: Luan C. Tran

Title: Methods of Forming Semiconductor Constructions

Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of co-pending application Serial No. 10/364,054, filed February 10, 2003. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: (JWY I) LOC

Bv:

ennifer J/Ta

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Form PTO-144	19	U.S. DEPARTMENT OF COMM PATENT AND TRADEMARK O				ATTY. DOCKET 1 M122-2356	NO.	NO. priority SER1/ 10/364,054		
		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Luan C. Tran			***************************************	
		,	(So with antibal income)			priority FILING D. February 10, 2003	prior 2812	priority GROUP 2812		
				U.S. PAT	ENT DOCUMENTS					
*Examiner Initial		Document Number	Date	Name			Class	Subclass	Filing If Appr	Date opriate
	AA	6,458,666 B2	10-2002	Wasshube	tshuber					
	AB	6,444,548 B2	09-2002	Divakarun	Divakaruni et al.					
AC		3,886,003	05-1975	Takagi et	al.					
	AD	4,366,338	12-1982	Turner et al.			T			
	AE	6,008,115	12-1999	Jung						
	AF	6,506,647 B2	01-2003	Kuroda et al.						
	AG	US2001/0036713A1	11-01-2001	Rodder et al.					July 5, 200	JI
	AH	US2002/0034865A1	03-21-2002	Unimoto et al.					Nov. 30, 20	001
	AI	09/876,722	1	Scott					June 6, 2001	
	AJ	10/133,193	1	McQueen et al.			<u> </u>		April 26, 2	1002
	AK		1				<u> </u>			
	AL	l	1				<u> </u>	<u></u>		
		Document	1	FOREIGN F	ATENT DOCUMENT	TS	T	T		
	Number		Date		Country		Class	Subclass	Yes	slation No
	AM			 -			├			
	AN	 	 	 				 	 	├
	AP		1				T	1		
			OTHER REFEREN	NCES (includi	ng Author, Title, Date	, Pertinent Pages, Etc.)				
	ΑQ	Young et al., "A 566, April 2000.	Young et al., "A 0.13 µm CMOS Technology with 193 nm Lithography and CulLow-k for High Performance Applications", IEDM, pgs. 563-566, April 2000.							pgs. 563-
	AR	Yeh et al., "Opti pgs. 2357-2362.	Yeh et al., "Optimum Halo Structure for Sul-0.1 µm CMOSPETIs", IEEE Transactions on Electronic Devices, Vol. 48, No. 10, October 2001 pgs. 2357-2362.							ober 2001,
	AS	Bouillon et al., "I that date is not i	Bouillon et al., "Re-examination of Indium implantation for a low power 0.1 µm technology", IDEM, pgs. 897-800, 1995 (year is sufficient so that date is not in issue).							